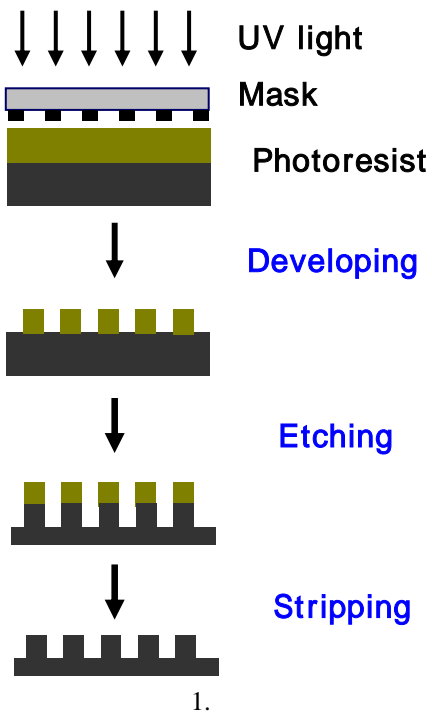


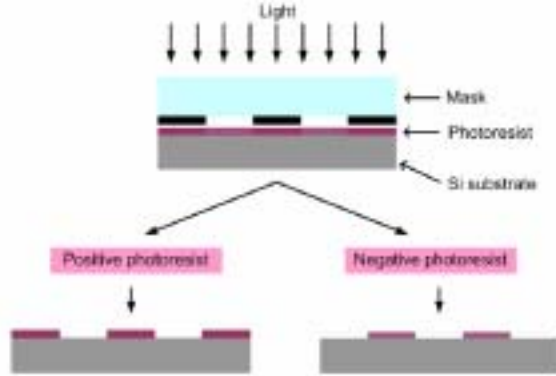
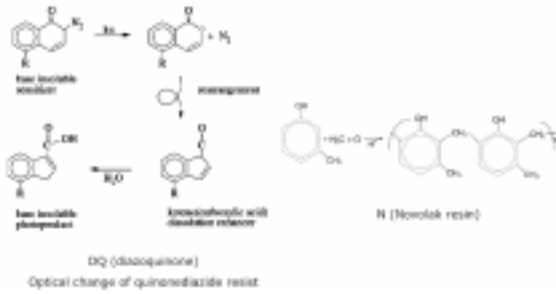
가

(photolithography)

(photoresist)



가



가

2 , 3

G/I line

2

(polymer),

3

(photoactive compound)

(solvent),

가

dissolution inhibitor

가

가

가가

Photo Acid Generator (PAG)가

가

가

가

$$\text{Resolution (R)} = K_1 * \lambda / \text{NA}$$

(1)

$$\text{DOF} = K_2 * \lambda / \text{NA}^2$$

(2)

λ , NA

, K_1 , K_2

. NA

focal length

DOF Depth of Focus

가

가

가

Diffraction

가

가

가

가

1.

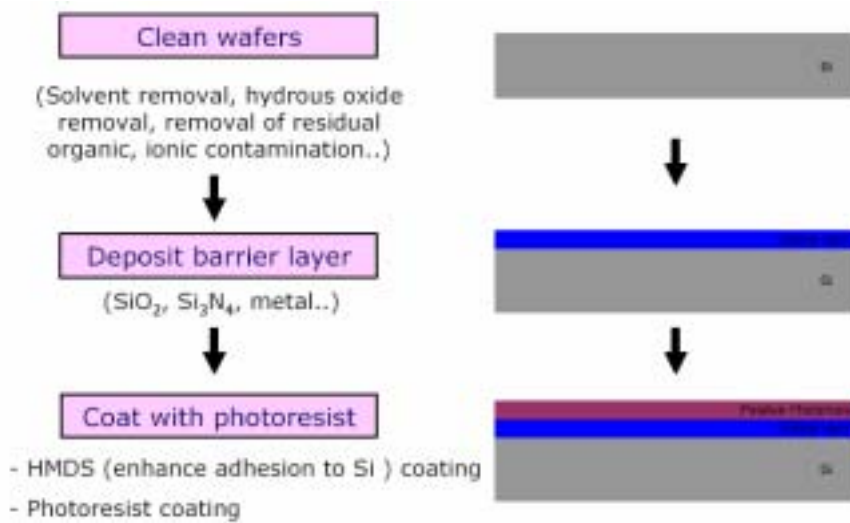
(Spin-Coating)

가

가

HMDS(Hexamethyldisilane) 2%

가



2.

2. Soft Bake

Soft bake

가

70~95°C

4~ 30

3. (Alignment)

(Exposure)

가

가

(Underdevelopment),

가

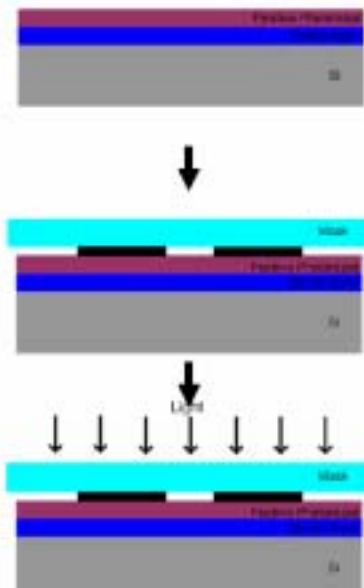
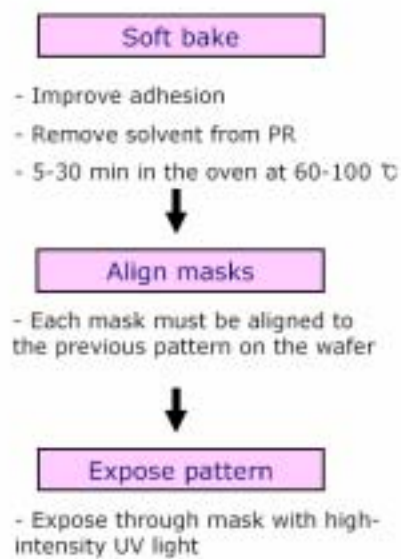
(Overdevelopment)

I

line(365nm)

KrF(248nm)

ArF(193nm)



3. Soft bake

4. (development)

Spray

